GRANDIS Pioneer in STT-RAM Technology

Director, MTJ Materials / Thin Film Development

Job Description:

Well funded start-up company with advanced non-volatile (spin-transfer torque) STT-RAM technology seeking a distinguished materials scientist to lead all research and development activities in magnetic tunnel junction (MTJ) materials and structures.

Responsibilities:

- Lead team of scientists and engineers developing novel materials and thin film multilayer structures for nanometer scale magnetic tunnel junctions (MTJs) for next-generation STT-RAM.
- Lead optimization of existing MTJ structures and thin-film processes for improved STT-RAM performance and yield.
- Lead research and development of new MTJ materials, structures and concepts for STT-RAM, from idea to full film evaluation to integrated device testing.
- Work with modeling, process integration, characterization, circuit design and chip testing teams to analyze data and feedback results to future experiments.
- Interface with collaborators at universities and government laboratories as part of the company's government-funded projects to develop STT-RAM.
- Recommend key equipment purchases to enhance the company's materials research and further improve cycle time from materials concept to device test.
- Transfer optimized MTJ materials and structures to the company's licensees and development partners for commercialization.
- Recruit and develop a world class team of materials scientists and engineers.
- Generate new ideas and contribute to the company's patent portfolio.

Required Skills:

- Exceptional knowledge and experience in materials science and device physics, with an emphasis on magnetic materials research and MTJ development.
- Hands-on experience with PVD systems and the full suite of magnetic material characterization equipment.
- Experience in taking materials development projects from concept to commercialization, either as a key scientific contributor or manager or both.
- Recognized as a technical leader by the wider scientific community, with frequent invited and contributed presentations at technical conferences.
- Knowledge in MRAM or STT-RAM devices and concepts a plus.
- Creative and analytical thinker, with a strong track record of generating new ideas and patents.
- Ability to work in and to foster an innovative environment in which new ideas are encouraged, not just from direct reports but from across the company.
- Strong and motivational leader, able to provide vision and inspire others, yet also not afraid to admit mistakes and change direction as required.

- Self-motivated, excellent teamwork skills, ability to multi-task, work and communicate effectively in fast paced environment.

Required Experience:

Extensive experience (> 10 years) of magnetic thin-film material and device development in the magnetic storage or MRAM industry. Several years' experience leading or managing a team of materials scientists or engineers is preferred.

Required Education:

Ph.D. in Materials Science, Physics, Applied Physics or Electrical Engineering.

Compensation:

We offer a very competitive compensation package that includes a stock option plan and a patent bonus program. Employees also receive medical, dental, vision and life insurance fully paid by the company, as well as a 401K plan. This position is located in Milpitas (Silicon Valley), California.